1-Bit Gate Pulse Modulator

The NLHV011 is a 1-bit gate pulse modulator designed to translate logic voltages for TFT LCD panels. This part translates a low voltage logic input signal to an output voltage of 15 V to 38 V. In addition, the NLHV011 provides a user selectable delay and fall time on the high-to-low edge of the output signal. The delay and fall times are controlled by the magnitudes of the external and capacitor resistor, respectively.

Features

- Gate Pulse Modulation (GPM)
- TFT LCD Flicker Compensation Circuit
- Reduction of Coupling Effect Between Gate Line and Pixel
- Provides Power Sequencing Circuit for Gate Driver IC
- Wide Power Supply Operation: 15 V to 38 V
- Adjustable Output Delay and Fall Time
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

• TFT LCDs

Important Information

• ESD Protection for All Pins: Human Body Model (HBM) > 3000 V

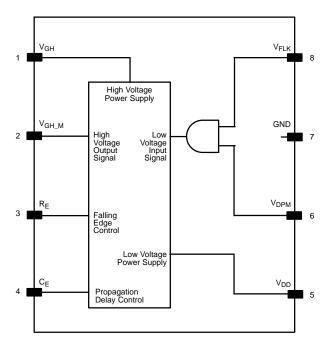


Figure 1. Block Diagram

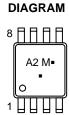


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US8 US SUFFIX CASE 493



MARKING

A2 = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

PIN DESCRIPTION

Pin	Pin Name	Pin Function	Comment
1	V_{GH}	Power Supply Input	V _{GH} = 15 to 38 V
2	V_{GH_M}	Output	This output directly drives the power supply of Gate Driver IC
3	R _E	R _E pin used to set the falling edge time (t _{fall})	The Delay time is programmed by connecting resistor R_{E} to V_{GH} and capacitor C_{E} to ground.
4	C _E	C _E pin used to set the propagation delay time (t _{phl})	
5	V _{DD}	Reference to input	The reference input pin is used to reduce flicker. The reference input voltage is as follows: $V_{DD} \le V_{GH} - 8.5 \text{ V}, V_{DD} = 0 \text{ to } 25 \text{ V}$
6	V _{DPM}	Signal input 1	V_{DPM} single input voltage is as follows: $V_{DPM} = 0 \text{ V to V}_{GH}$. The V_{DPM} pin is used to create a delay with the V_{GH} to prevent system latch–up. V_{DPM} also determines the time V_{GH} is ON.
7	GND	Ground	
8	V _{FLK}	Signal input 2	V _{FLK} single input voltage is as follows: V _{DPM} = 0 V to V _{GH} . The V _{FLK} determines the ON/OFF time of the TFT LCD and is produced from LCD timing controller module.

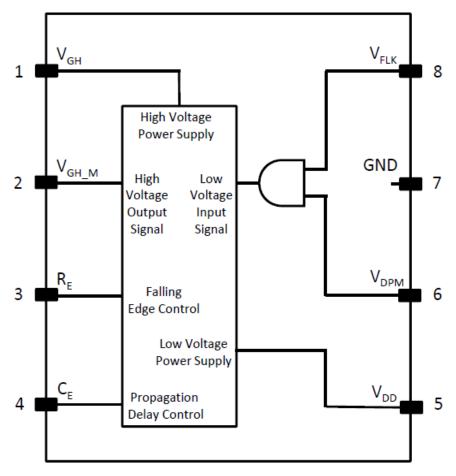


Figure 2. Block Diagram

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V_{GH}	DC Supply Voltage		-0.5 to +40	V
V_{DD}	DC Supply Voltage		-0.5 to +40	V
V_{FLK}	Input Voltage V _{FLK}		-0.5 to +40	V
V_{DPM}	Input Voltage V _{DPM}		-0.5 to +40	V
V _{GH} – V _{CE}	Differential Voltage Between V_{GH} and V_{CE} Pins (Note 1)		9.5	V
I _{IK}	DC Input Diode Current		±50	mA
l _{OK}	DC Output Diode Current		±50	mA
I _O	DC Output Current		50	mA
I _{GH}	DC Supply Current Per Supply Pin		50	mA
P_{D}	Power Dissipation		200	mW
T_J	Junction Temperature		95	°C
T _{STG}	Storage Temperature		-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V_{GH}	DC Supply Voltage (Note 2)	$V_{GH} - V_{DD} \ge 8.5 \text{ V}$	15	-	38	V
V_{DD}	DC Supply Voltage	$V_{DD} \le V_{GH} - 8.5 \text{ V}$	0	-	25	V
V _{FLK}	Input Voltage V _{FLK}	V _{GH_M} = V _{GH} – 1.2 V	1.5	-	V_{GH}	V
V_{DPM}	Input Voltage V _{DPM}	V _{GH_M} = V _{DD} + 1.5 V	0	-	V_{GH}	V
T _A	Operating Temperature Range		-40	-	85	V
V _{GH} – V _{CE}	Differential Voltage Between V _{GH} and V _{CE} Pins (Note 3)		-	_	5.5	V
		C _E = 5 pF		0.2		
		C _E = 10 pF		0.4		
		C _E = 50 pF		0.6		
Δt / ΔV_{GH}	Safe V _{GH} Power–Up Slew Rate (Note 4)	C _E = 150 pF	_	0.7	_	μs / V
		C _E = 220 pF		0.8		
		C _E = 500 pF		1.2		
		C _E = 1000 pF		2.2		

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- 2. Maximum recommended V_{GH} supply voltage guaranteed by design.
- A differential voltage between the V_{GH} and V_{CE} pins (V_{GH} V_{CE}) occurs during the power-up and power-down procedure. The voltages on the V_{GH} and C_E pins are equal at steady-state conditions after power-up.
- 4. It is recommended that a ceramic or tantalum decoupling capacitor of 0.1 to 1 μF is used on the V_{GH} power supply voltage. The capacitor should be placed adjacent to the NLHV011 and connected between V_{GH} and Ground.

A differential voltage between the V_{GH} and V_{CE} pins (V_{GH} - V_{CE}) occurs during the power-up and power-down procedure. The voltages on the V_{GH} and C_E pins are equal at steady-state conditions after power-up.

ELECTRICAL CHARACTERISTICS (V_{GH} = 20 V, V_{DD} = 10 V, V_{DPM} = 2.2 V, V_{FLK} = 2.2 V, V_{GH} – V_{DD} \geq 8.5 V, T_a = 25 °C, unless otherwise noted.)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _{FLK_H}	FLK High Voltage	V _{GH_M} = V _{GH} – 1.6	1.5	_	V_{GH}	V
V _{FLK_L}	FLK Low Voltage	V _{GH_M} = V _{DD} + 1.5	0	_	0.5	V
V _{DPM_H}	DPM High Voltage	$V_{FLK} = 0 \text{ V}, V_{GH_M} = V_{DD} - 0.2 \text{ V}$	1.5	_	V_{GH}	V
V _{DPM_L}	DPM Low Voltage	$V_{FLK} = 0 \text{ V}, V_{GH_M} \le 0.6 \text{ V}$	0	-	0.5	V
I _{DPM}	DPM ON Current	$V_{FLK} = 3 \text{ V}, V_{GH_M} = V_{GH}$	0.2	0.4	2	mA
R _C	R _C (Resistor of V _{DPM} pin)	V_{GH} = 22 V, $R_C \approx (V_{GH} - 0.9)$ / I_{DPM} (Application Circuits 2 and 3)	10	45	100	kΩ
V _{GH_M, H}	Output High Voltage	I _O = 10 mA	V _{GH} – 1.6	V _{GH} – 0.7	-	V
V _{GH_M, R}	Output Reset Voltage	V _{DPM} = 0 V, V _{FLK} = 3 V			0.6	V
		V _{DPM} = 0 V, V _{FLK} = 0 V	_	_		V
V _{GH_M, L}	Output Low Voltage	$V_{DPM} = 3 \text{ V, } V_{FLK} = 0 \text{ V,}$ $I_{O} = -1 \text{ m A}$	V _{DD} – 0.2	V _{DD} + 0.3	V _{DD} + 0.8	V
I _{GH}	Power Supply Input Current	$V_{GH} = 35 \text{ V}, V_{DD} = 15 \text{ V},$ $V_{FLK} = V_{DPM} = 3.3 \text{ V}, I_{O} = 0$	-	3.5	-	mA
I _{DD}	Reference Input Current	V _{GH} = 35 V, V _{DD} = 15 V, V _{FLK} = 0 V, V _{DPM} = 3.3 V, I _O = 0	-	40	-	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

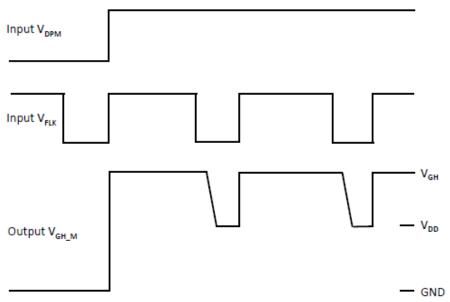


Figure 3. Input and Output Waveforms (Application Circuit #1)

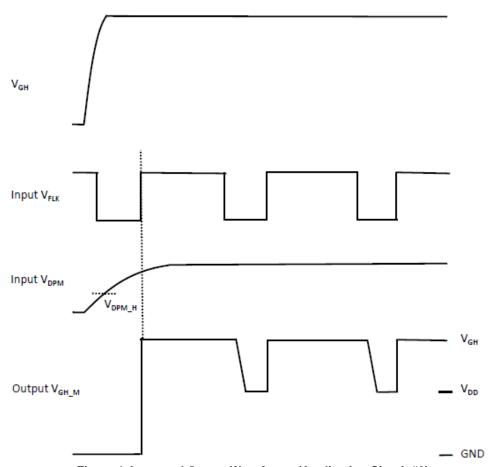


Figure 4. Input and Output Waveforms (Application Circuit #2)

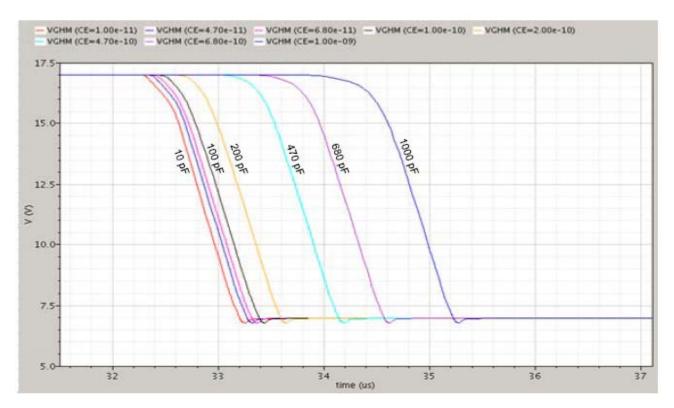


Figure 5. V_{GH_M} Output Propagation Delay (t_{phl}) is controlled by C_E (Application Circuit #1, V_{GH} = 18 V, V_{DD} = 7 V, R_E = 3.9 k Ω , R_L = 15 k Ω , C_L = 220 pF, T_a = 25 °C)

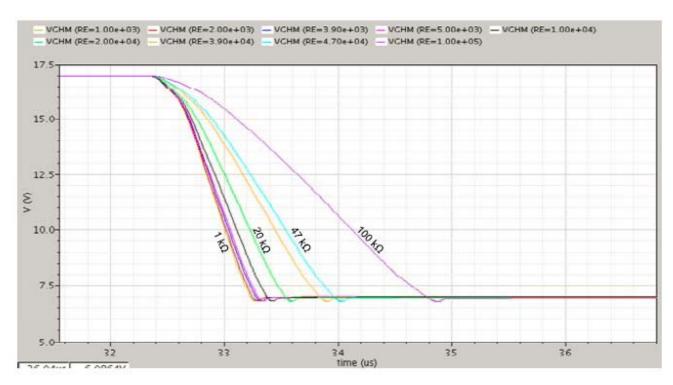
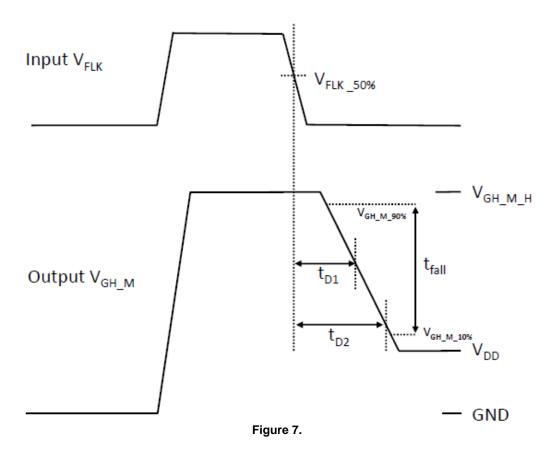


Figure 6. V_{GH_M} Output Transition Falling Edge (t_{fall}) is controlled by R_E (Application Circuit #1, V_{GH} = 18 V, V_{DD} = 7 V, C_E = 47 pF, R_L = 15 k Ω , C_L = 220 pF, T_a = 25 °C)



Definition of Delay Time

 $\begin{array}{l} t_{D1} = \text{Delay Time 1} \; (t_{D_50-50}) = V_{FLK_50\%} \; \text{to} \; [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \; x \; 0.50)] \\ t_{D2} = \text{Delay Time 2} \; (t_{D_50-15}) = V_{FLK_50\%} \; \text{to} \; [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \; x \; 0.15)] \\ \end{array}$

 $t_{fall} = 90 - to - 10\% \ Fall \ Time = [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.90)] - [V_{DD} + ((V_{GH_M_H}) - V_{DD}) \ x \ 0.10)]$

DELAY TIME CHARACTERISTICS

(Application Circuit #1, V_{DPM} = 3 V, V_{FLK} = 3 V, R_E = 15 k Ω , R_L = 15 k Ω , C_L = 220 pF, T_A = 25°C)

Parameter	Test Condition	Тур	Unit
	$V_{GH} = 17 \text{ V}, V_{DD} = 6.7 \text{ V}, C_E = 100 \text{ pF}$	2.4	μs
	$V_{GH} = 17 \text{ V}, V_{DD} = 6.7 \text{ V}, C_E = 240 \text{ pF}$	2.8	μs
Dolov Timo 2 (t-	$V_{GH} = 22.4 \text{ V}, V_{DD} = 10 \text{ V}, C_E = 91 \text{ pF}$	2.3	μs
Delay Time 2 (t _{D_50-15})	$V_{GH} = 22 \text{ V}, V_{DD} = 10 \text{ V}, C_E = 220 \text{ pF}$	2.8	μs
	$V_{GH} = 25.4 \text{ V}, V_{DD} = 15.4 \text{ V}, C_{E} = 56 \text{ pF}$	2.4	μs
	$V_{GH} = 25.4 \text{ V}, V_{DD} = 15.4 \text{ V}, C_E = 130 \text{ pF}$	2.5	μs

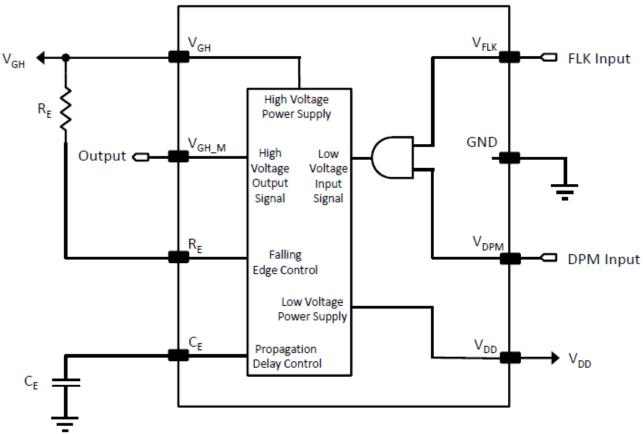


Figure 8. Application #1 Circuit Schematic

Notes:

1. V_{DPM} can rise only after V_{GH} is valid.

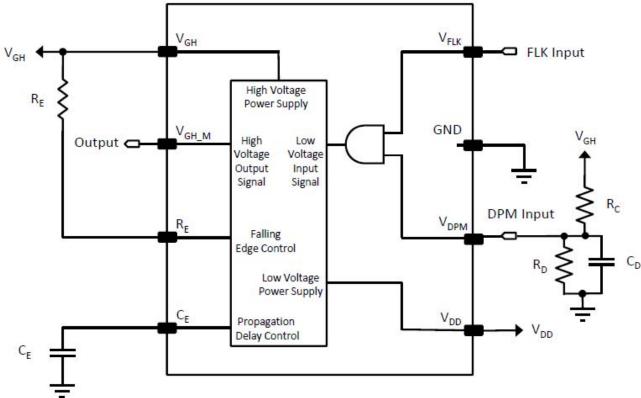


Figure 9. Application #2 Circuit Schematic

Notes:

- 1. V_{DPM} is produced by a Low Pass Filter (LPF) on V_{GH} pin with R_{C} and C_{D} .
- 2. R_D is a V_{DPM} pull-down resistor.

APPLICATION 2: $V_{\text{GH_M}}$ SIGNAL DELAY TIME CHARACTERISTICS

V _{GH} (V)	V _{DD} (V)	C _D (μF)	R _D (kΩ)	R _C (kΩ)	V _{GH_M} ON Delay Time (when V _{GH} ON) t _{on} (ms)	V _{DPM} Pin Discharge Time (when V _{GH} OFF) t _{off} (ms)
		1	15	50	17.9	3.4
22	12	1	1.5	20	5.5	1.4
		1	0.620	10	1.7	0.74

APPLICATION 2: FUNCTION DESCRIPTION

Name	Comment	Function
R _C	R _C and C _D determines the time when the V _{DPM} pin is	
C _D	charged.	t_{on} = Time when V_{GH_M} is high
R _D	R_{D} determines the time when the V_{DPM} pin is discharged.	t_{off} = Time when V_{DPM} pin is fully discharged

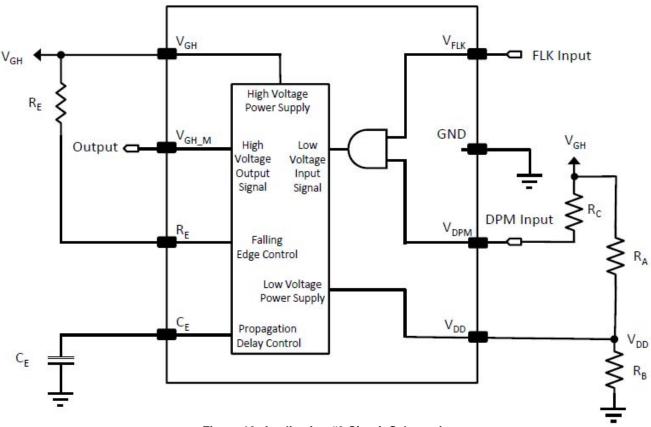


Figure 10. Application #3 Circuit Schematic

APPLICATION 3: FUNCTION DESCRIPTION

Name	Comment	Function
R _A	R_A and R_B set the V_{DD} voltage.	$V_{DD} = V_{GH} \times (R_B / (R_A + R_B))$
R _B		
R _C	R_{C} determines the voltage that V_{DPM} pin becomes high.	

Notes:

- 1. V_{DPM} produced by external R_{C} and internal R and C.
- 2. V_{DD} created from external resistors R_A and R_B .
- 3. V_{GH} should be higher than 18 V to meet V_{DPM_H} . 4. R_A = 15 k Ω , R_B = 10 k Ω , R_C = 45 k Ω , R_E = 15 k Ω , R_L = 15 k Ω , C_E = 220 pF, C_L = 100 pF

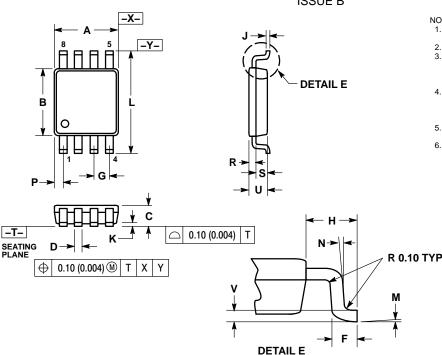
DEVICE ORDERING INFORMATION

	Device Order Number	Package Type	Shipping [†]
NLHV0	11USG	US8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

US8 CASE 493-02 **ISSUE B**

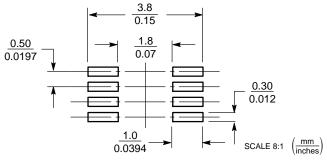


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD
- FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.
- LEAD FINISH IS SOLDER PLATING WITH
- THICKNESS OF 0.0076-0.0203 MM. (300-800 "). ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 ").

		MILLIMETERS		INC	INCHES		
	DIM	MIN	MAX	MIN	MAX		
	Α	1.90	2.10	0.075	0.083		
	В	2.20	2.40	0.087	0.094		
	C	0.60	0.90	0.024	0.035		
	D	0.17	0.25	0.007	0.010		
	F	0.20	0.35	0.008	0.014		
	G	0.50	BSC	0.020	BSC		
	Н	0.40	REF	0.016 REF			
)	7	0.10	0.18	0.004	0.007		
	K	0.00	0.10	0.000	0.004		
	L	3.00	3.20	0.118	0.126		
	М	0°	6 °	0°	6 °		
	Z	5°	10 °	5 °	10 °		
	Р	0.23	0.34	0.010	0.013		
	R	0.23	0.33	0.009	0.013		
	s	0.37	0.47	0.015	0.019		
	כ	0.60	0.80	0.024	0.031		
	V	0.12	BSC	0.005	BSC		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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